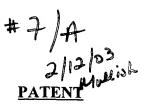
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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Minh Van NGO, et al.

Serial No.: 09/986,267

Filed: November 08, 2001

For:

/

Group Art Unit: 2812

Examiner: J. Brophy

: METHOD OF FORMING RELIABLE CU INTERCONNECTS

## <u>AMENDMENT</u>

Commissioner for Patents Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office Action dated November 1, 2002.

## IN THE CLAIMS:

Please amend claim 10 as follows.

10. (Amended) The method according to claim 9, comprising:

treating the upper surface of the Cu or Cu alloy in a plasma containing [NH<sub>4</sub>]  $\underline{\text{NH}}_3$  to remove copper oxide therefrom; and

depositing a silicon nitride capping layer on the plasma treated surface by plasma enhanced chemical vapor deposition.

Please add new claim 16 as follows.